



B

It combines advanced trench MOSFET technology with a low resistance package tenes advanced tencer

$T_C=25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_{D@TC=25}$	240	A
	$I_{D@TC=75}$	182	A
	$I_{D@TC=100}$	151	A
Pulsed Drain Current	I_{DM}	720	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	150	W
Total Power Dissipation($TA=25$)	$P_D@TA=25$	3.1	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	1760	mJ



Fig.1 Power Dissipation

Fig.2 Typical output Characteristics

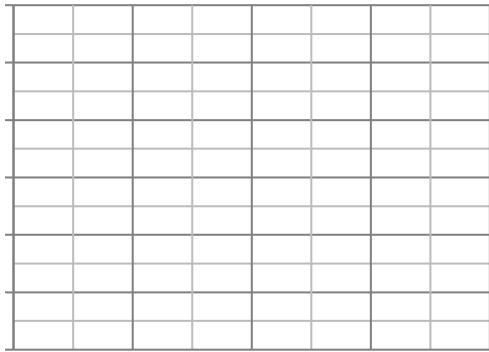


Fig.3 Threshold Voltage V.S Junction Temperature

Fig.4 Resistance V.S Drain Current

Fig.5 On-Resistance VS Gate Source Voltage

Fig.6 On-Resistance V.S Junction Temperature



Unit mm

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.42		4.72	E	8.99		9.29
B	1.22		1.32	e1	2.44		2.64
b	0.76		0.86	e2	4.98		5.18
b1	1.22		1.32	L1	15.19		15.79
b2	0.33		0.43	L2	2.29		2.79
C	1.22		1.32	L3	1.3		1.75
D	9.95		10.25				

